



MOS FET
FK3906010L

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Silicon N-channel MOSFET

For switching
FK350601 in SSMini3 type package

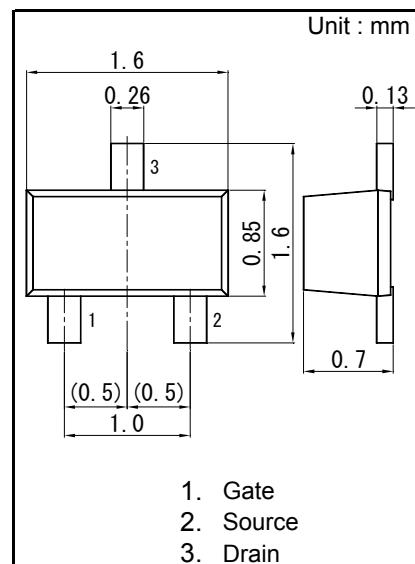
■ Features

- Low drive voltage : 2.5 V drive
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol : CV

■ Packaging

Embossed type (Thermo-compression sealing) : 3 000 pcs / reel (standard)

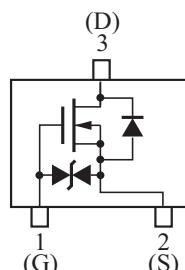


■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Drain-source voltage	VDS	60	V
Gate-source voltage	VGS	±12	V
Drain current	ID	100	mA
Pulse drain current	IDp	200	mA
Total power dissipation	PD	125	mW
Channel temperature	Tch	150	°C
Operating ambient temperature	Topr	-40 to + 85	°C
Storage temperature	Tstg	-55 to +150	°C

Panasonic	SSMini3-F3-B
JEITA	SC-89
Code	SOT-490

Internal Connection



Pin Name

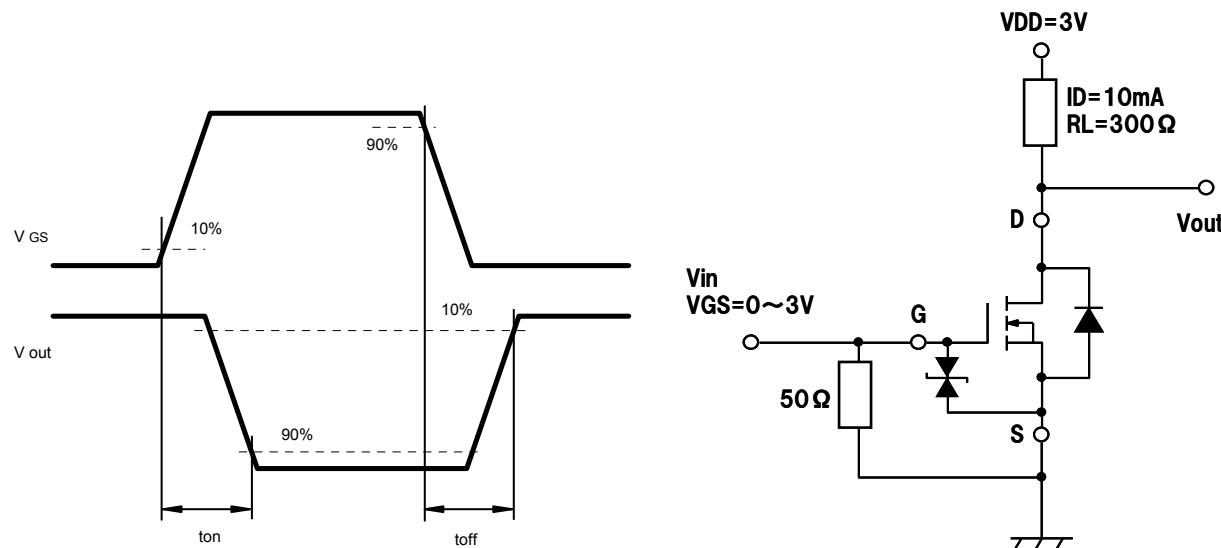
1. Gate
2. Source
3. Drain

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

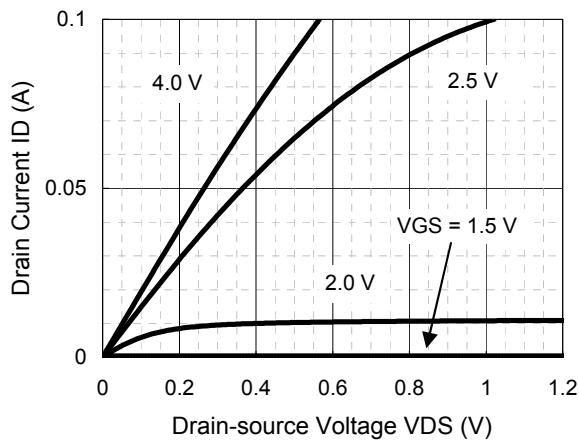
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source breakdown voltage	VDSS	ID = 1 mA, VGS = 0	60			V
Drain-source cutoff current	IDSS	VDS = 60 V, VGS = 0			1.0	μA
Gate-source cutoff current	IGSS	VGS = ± 10 V, VDS = 0			± 10	μA
Gate threshold voltage	VTH	ID = 1.0 μA , VDS = 3.0 V	0.9	1.2	1.5	V
Drain-source ON resistance	RDS(on)	ID = 10 mA, VGS = 2.5 V		8	15	Ω
		ID = 10 mA, VGS = 4.0 V		6	12	Ω
Forward transfer admittance	Yfs	ID = 10 mA, VDS = 3.0 V	20	60		mS
Input capacitance	Ciss			12		pF
Output capacitance	Coss	VDS = 3 V, VGS = 0, f = 1 MHz		7		pF
Reverse transfer capacitance	Crss			3		pF
Turn-on time ^{*1}	ton	VDD = 3 V, VGS = 0 to 3 V, ID = 10 mA		100		ns
Turn-off time ^{*1}	toff	VDD = 3 V, VGS = 3 to 0 V, ID = 10 mA		100		ns

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

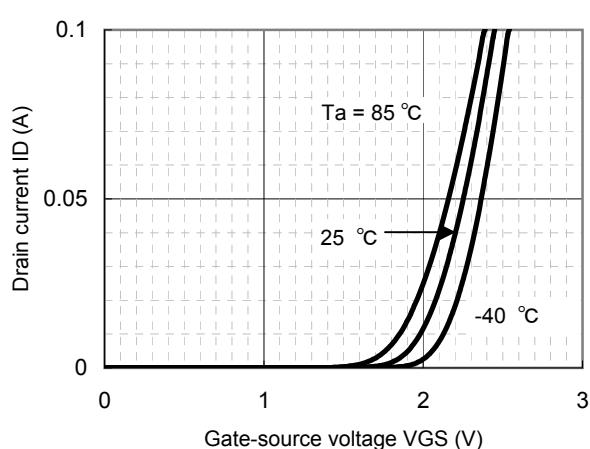
2. *1 Turn-on and Turn-off test circuit



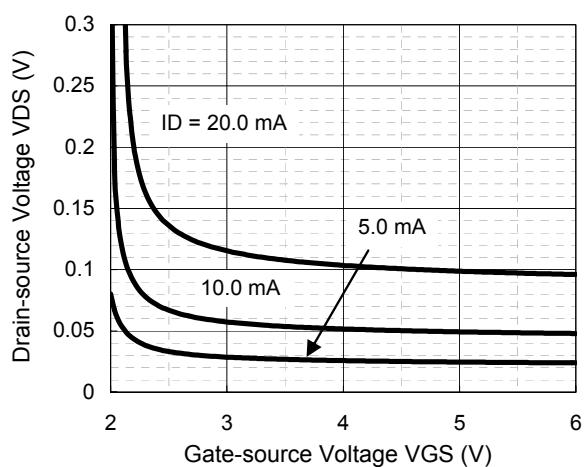
ID - VDS



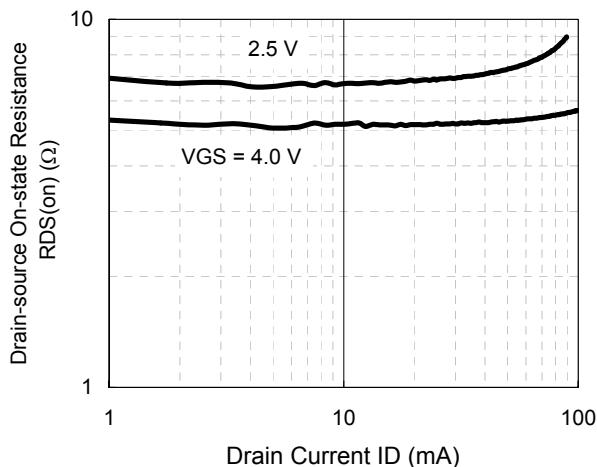
ID - VGS



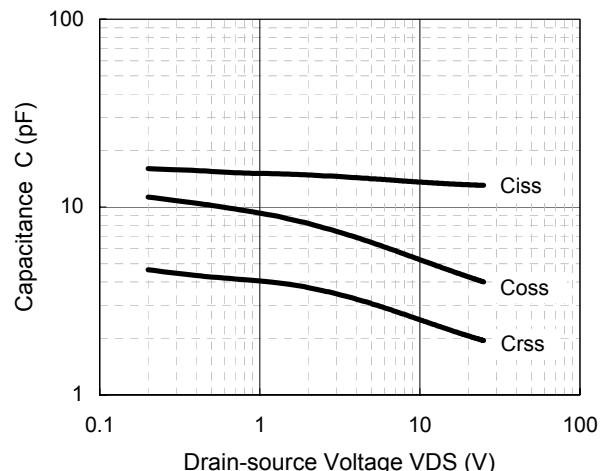
VDS - VGS



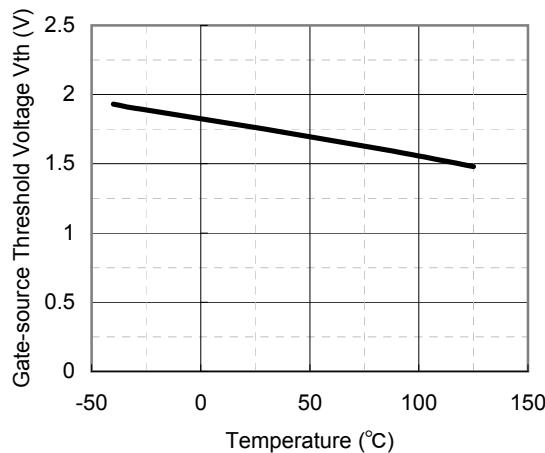
RDS(on) - ID



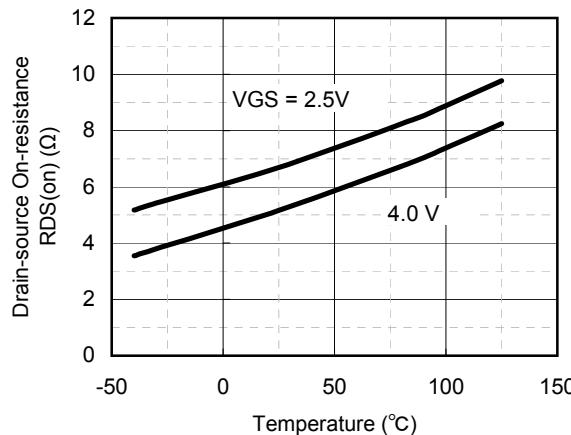
Capacitance - VDS



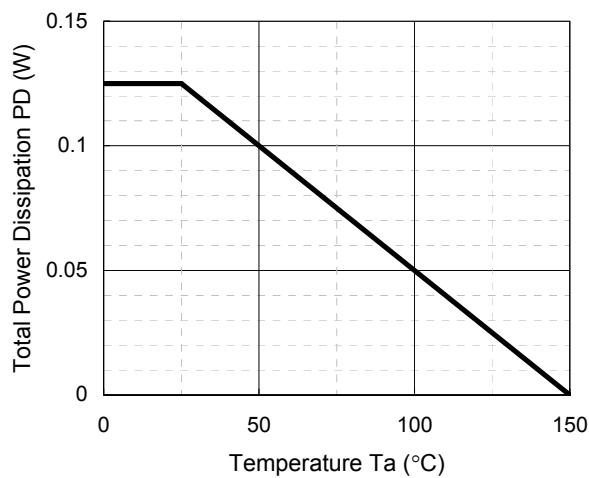
V_{th} - Ta



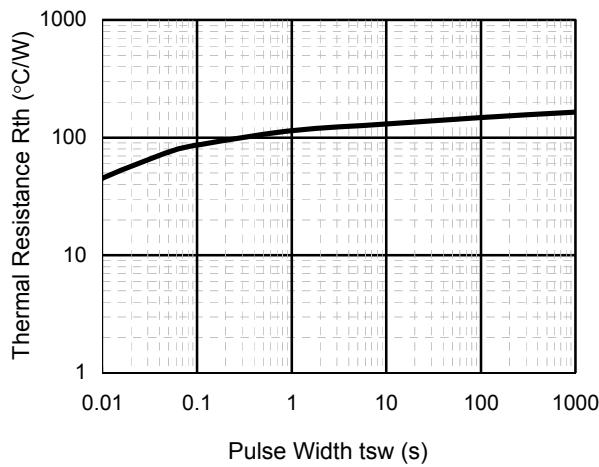
RDS(on) - Ta



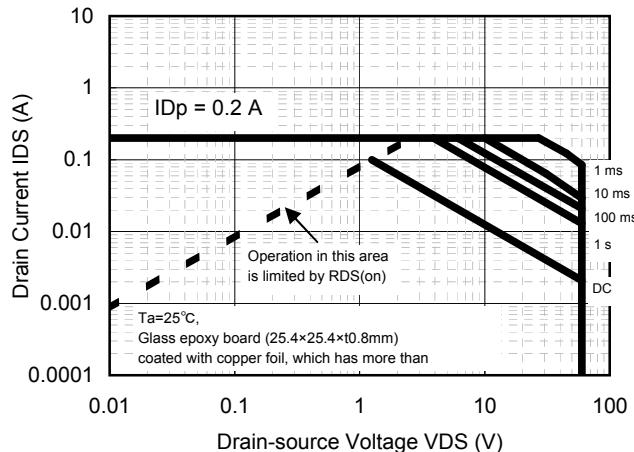
PD - Ta



R_{th} - tsw



Safe Operating Area

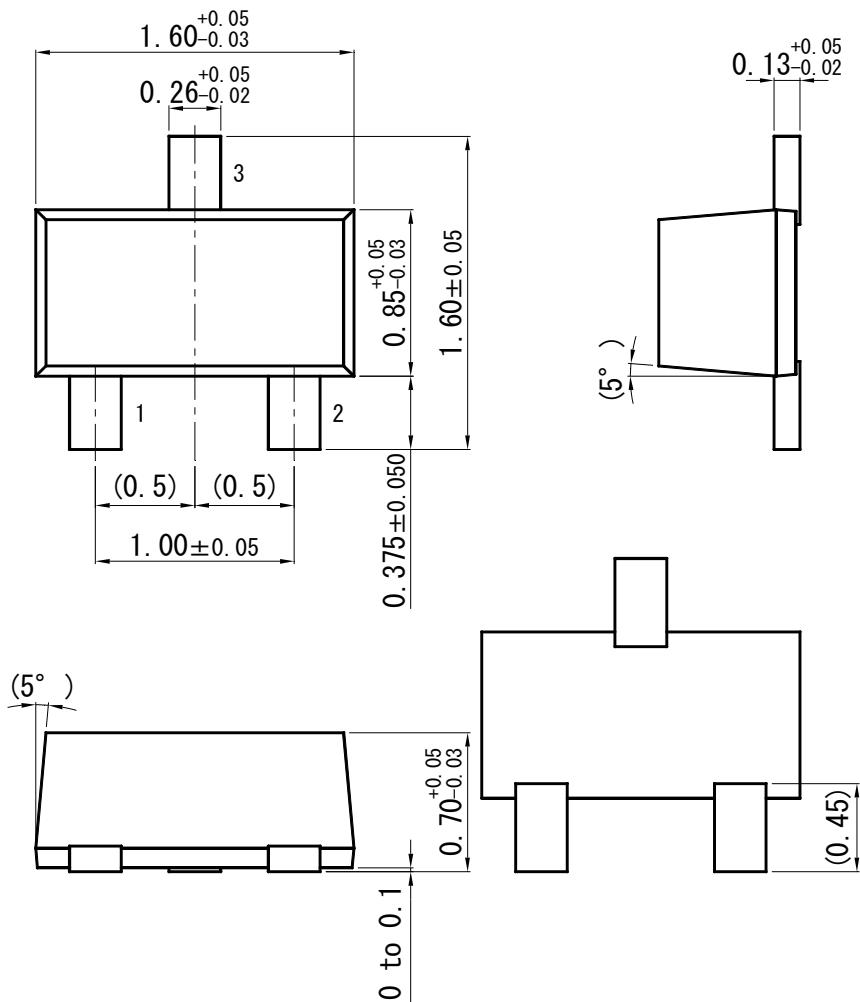


Panasonic

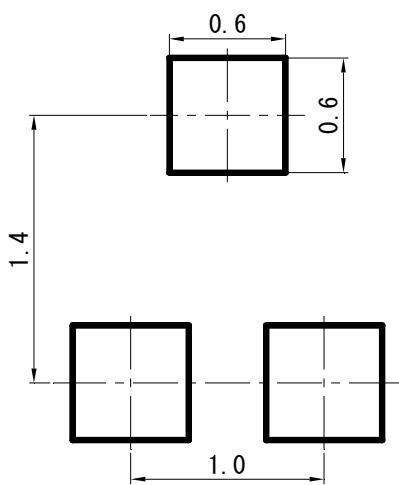
MOS FET
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SSMini3-F3-B

Unit : mm



■ Land Pattern (Reference) (Unit : mm)



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